

20 V, 6.3 A PNP/PNP low V_{CEsat} (BISS) transistor Rev. 2 — 11 October 2010 Pro

Product data sheet

Product profile 1.

1.1 General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT96-1 (SO8) medium power Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

Type number	Package I		NPN/NPN	NPN/PNP	
	Nexperia	Name	complement	complement	
PBSS4021SP	SOT96-1	SO8	PBSS4021SN	PBSS4021SPN	

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FF}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-20	V
I _C	collector current		-	-	-6.3	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-	-15	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -5 A; I _B = -0.5 A	<u>1]</u> _	36	54	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	emitter TR2		
4	base TR2		
5	collector TR2		1 2 3 4
6	collector TR2		006aaa976
7	collector TR1		
8	collector TR1		

3. Ordering information

Table 4. Orde	ring inform	nation	
Type number Package			
	Name	Description	Version
PBSS4021SP	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Marking

Table 5.	Marking codes	
Type num	ber	Marking code
PBSS402	1SP	4021SP

5. Limiting values

Table 6.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-20	V
V _{CEO}	collector-emitter voltage	open base	-	-20	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-6.3	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-15	А
I _B	base current		-	-1	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	0.73	W
			[2] -	1	W
			[3] _	1.7	W

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Symbol	Parameter	Conditions	Min	Max	Unit
Per device	l.				
P _{tot} total power dissipation		$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	0.86	W
			[2] _	1.4	W
			[3] _	2.3	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

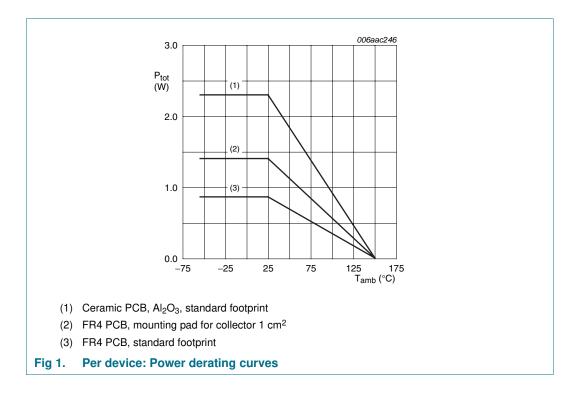
 Table 6.
 Limiting values ... continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



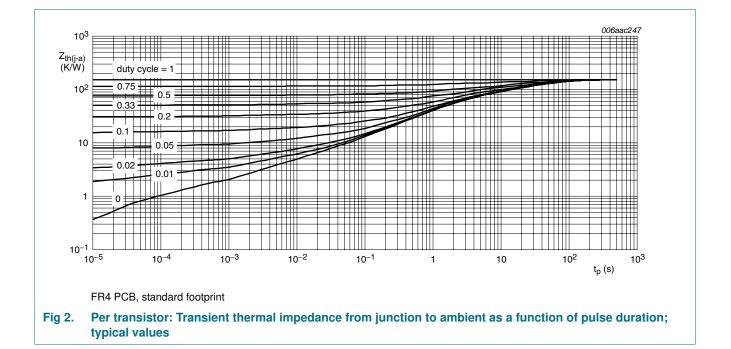
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6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per trans	istor					
R _{th(j-a)} thermal resistance from		in free air	<u>[1]</u> -	-	170	K/W
	junction to ambient		[2] _	-	125	K/W
			[3] _	-	75	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	40	K/W
Per devic	e					
R _{th(j-a)}	thermal resistance from	in free air	[1] -	-	145	K/W
	junction to ambient		[2] _	-	90	K/W
			[3] _	-	55	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

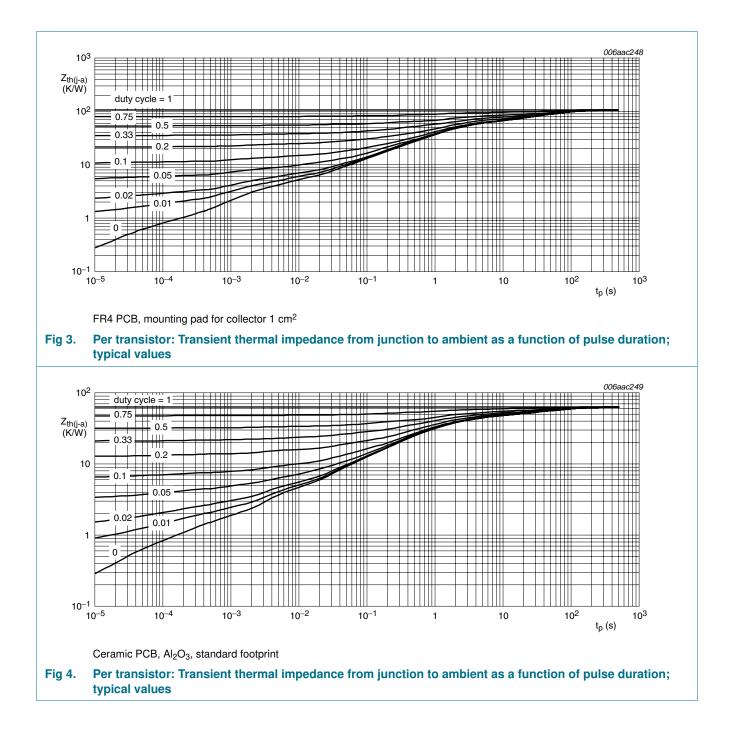


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7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
I _{CBO}	collector-base	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
	cut-off current	$\label{eq:VCB} \begin{array}{l} V_{CB} = -20 \ V; \ I_E = 0 \ A; \\ T_j = 150 \ ^\circ C \end{array}$		-	-	-50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -16 \text{ V}; V_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 V$	[1]				
		I _C = -500 mA		250	400	-	
		$I_{\rm C} = -1$ A		250	400	-	
		$I_{\rm C} = -2$ A		200	350	-	
		$I_{\rm C} = -4$ A		150	300	-	
		$I_{\rm C} = -7$ A		80	200	-	
V _{CEsat} collector-emitter			[1]				
saturation	saturation voltage	$I_{C} = -1$ A; $I_{B} = -50$ mA		-	-45	-68	mV
		$I_{C} = -1 \text{ A}; I_{B} = -10 \text{ mA}$		-	-70	-115	mV
		$I_{C} = -2 \text{ A}; I_{B} = -40 \text{ mA}$		-	-100	-150	mV
		$I_{C} = -4 \text{ A}; I_{B} = -200 \text{ mA}$		-	-150	-225	mV
		$I_{C} = -4 \text{ A}; I_{B} = -40 \text{ mA}$		-	-250	-375	mV
		$I_{C} = -6.5 \text{ A}; I_{B} = -325 \text{ mA}$		-	-235	-350	mV
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -5 \text{ A}; I_{B} = -500 \text{ mA}$	[1]	-	36	54	mΩ
V _{BEsat}	base-emitter		[1]				
	saturation voltage	$I_{C} = -1 \text{ A}; I_{B} = -100 \text{ mA}$		-	-0.85	-1	V
		$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$		-	-1	-1.2	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$	<u>[1]</u>	-	-0.76	-0.85	V
t _d	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -1 \text{ A};$		-	40	-	ns
t _r	rise time	$I_{Bon} = -0.05 \text{ A}; I_{Boff} = 0.05 \text{ A}$		-	55	-	ns
t _{on}	turn-on time			-	95	-	ns
ts	storage time			-	340	-	ns
t _f	fall time			-	85	-	ns
t _{off}	turn-off time			-	425	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_C = -100 \text{ mA};$ f = 100 MHz		-	105	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz		-	95	-	pF

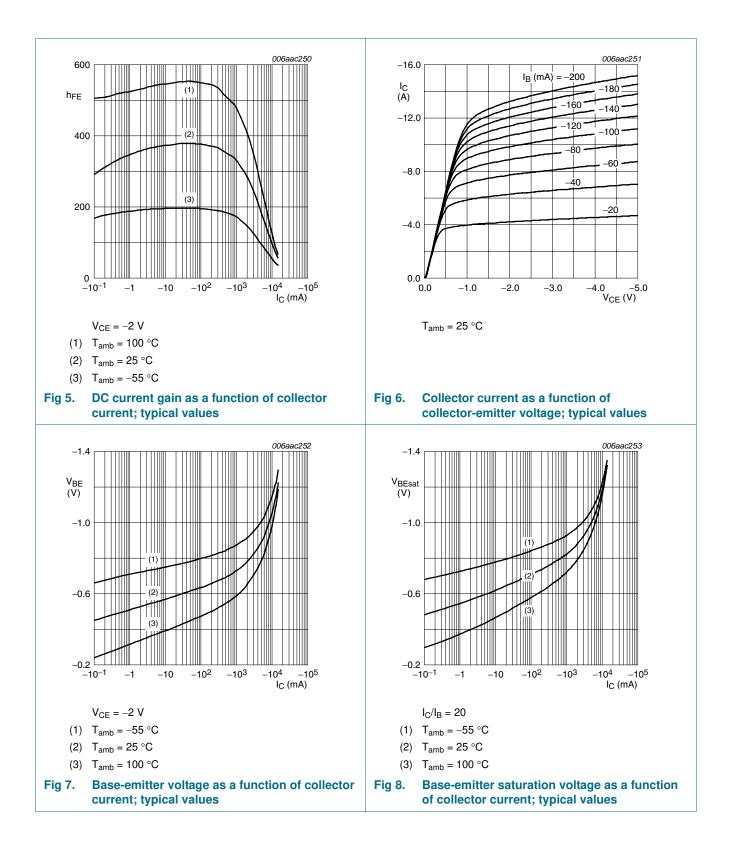
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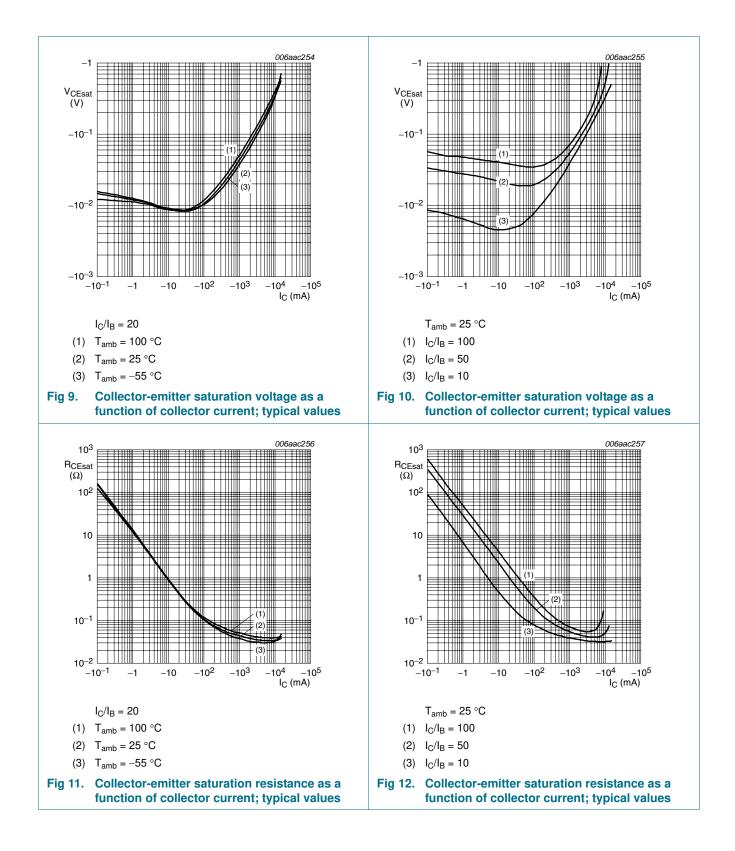
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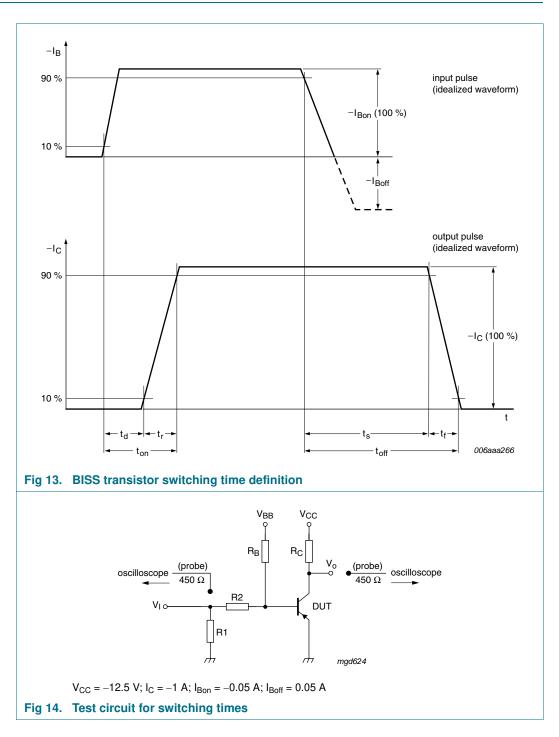
PBSS4021SP

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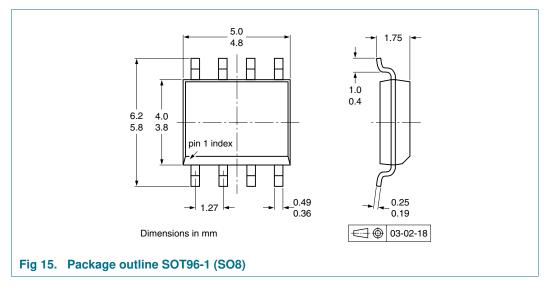
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8. Test information



20 V, 6.3 A PNP/PNP low V_{CEsat} (BISS) transistor

9. Package outline



10. Packing information

Table 9. Packing methods

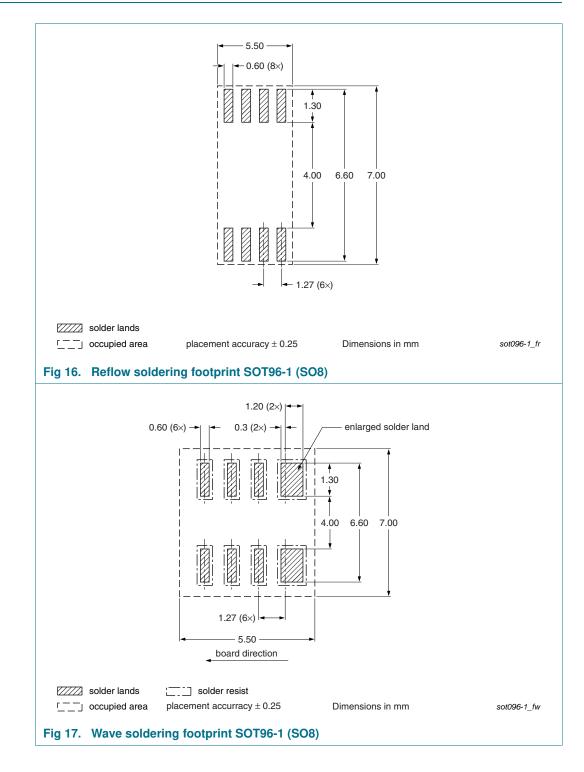
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	number Package Description Packing quantity		quantity	
			1000	2500
PBSS4021SP	SOT96-1	8 mm pitch, 12 mm tape and reel	-115	-118

[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 10. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021SP v.2	20101011	Product data sheet	-	PBSS4021SP v.1
Modifications:	 Figure 1 "Pe 	er device: Power derating c	urves": updated.	
PBSS4021SP v.1	20100714	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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